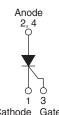
**Vishay Semiconductors** 

# Thyristor, Surface Mount, Phase Control SCR, 16 A



www.vishay.com



D<sup>2</sup>PAK (TO-263AB)

Cathode Gate

PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	16 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V						
V <sub>TM</sub>	1.25 V						
I <sub>GT</sub>	45 mA						
TJ	-40 to +125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

## **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 gualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- · Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### DESCRIPTION

The VS-25TTS12SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m$ ) copper	3.5	5.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0						

### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Α				
I <sub>RMS</sub>		25					
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V				
I <sub>TSM</sub>		350	A				
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		-40 to +125	°C				

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> , AT 125 °C mA						
VS-25TTS12SLHM3	1200	1200	10						

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL				UES		
PARAMETER	STNIDUL	153	T CONDITIONS	TYP.	MAX.		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	conduction half sine wave	1			
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	А	
Maximum peak, one-cycle,		10 ms sine pulse,	rated V <sub>RRM</sub> applied	3	00	A	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse,	no voltage reapplied	3	50		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse,	rated V <sub>RRM</sub> applied	4	50	A <sup>2</sup> s	
	1-1	10 ms sine pulse, no voltage reapplied			30	A-5	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 m	6300		A²√s		
Maximum on-state voltage drop	V <sub>TM</sub>	16 A, T <sub>J</sub> = 25 °C	1.25		V		
On-state slope resistance	r <sub>t</sub>	7 107.00			2.0	mΩ	
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.0		V	
Maximum rayaraa and diraat laakaga ayrrant	1 /1	T <sub>J</sub> = 25 °C	$V_{\rm c}$ = Poted $V_{\rm c}$ = $\Lambda/$	0.5		-	
Maximum reverse and direct leakage current	I <sub>RM</sub> / I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10			
Holding current	I <sub>H</sub>	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1 A$ , $T_J = 25 \text{ °C}$			mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs	
Maximum rate of rise of turned-on current	di/dt			1:	A∕µs		

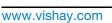
TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P <sub>GM</sub>		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv					
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	А					
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V					
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	60	mA					
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	45						
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20						
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	2.5						
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0						
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V					
Maximum DC gate voltage not to trigger	V <sub>GD</sub>	T 105 % V retectively	0.25						
Maximum DC gate current not to trigger	I <sub>GD</sub>	$T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$	2.0	mA					

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T 105 %	4	μs				
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110					

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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/W				
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TTS	S12SH				

### Note

(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

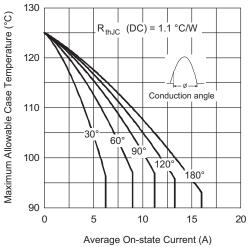
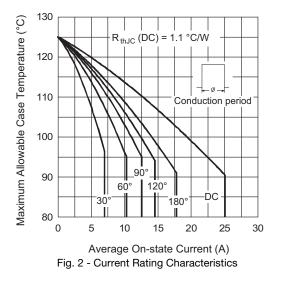


Fig. 1 - Current Rating Characteristics



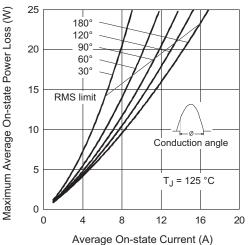
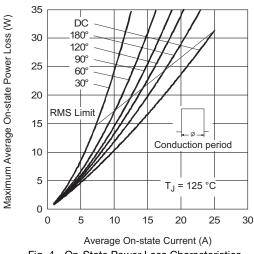


Fig. 3 - On-State Power Loss Characteristics





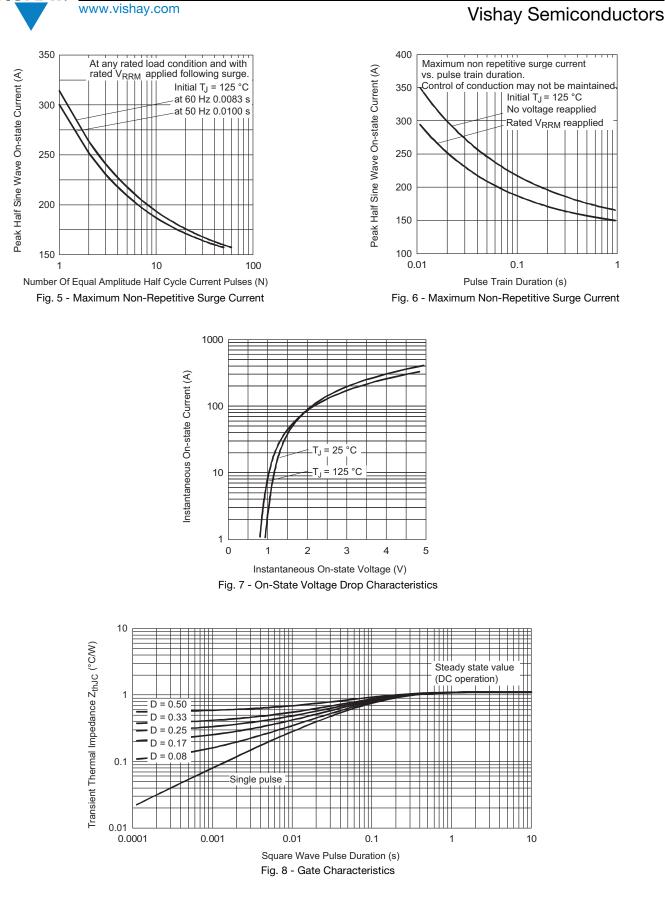
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# VS-25TTS12SLHM3

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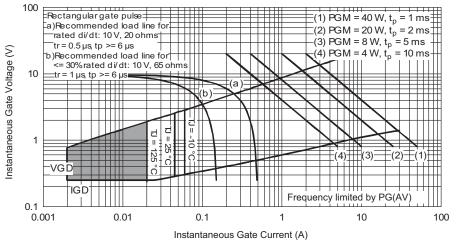


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

## **ORDERING INFORMATION TABLE**

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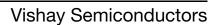
Device code	VS-	25	т	т	S	12	S	L	н	М3	
	1	2	3	4	5	6	(7)	8	9	10	
	1 - Vishay Semiconductors product										
	2 -	<b>2</b> - Current rating (25 = 25 A)									
	3 -		Circuit configuration: T = single thyristor								
	4 -		Package: T = D <sup>2</sup> PAK (TO-263AB)								
	5 -		e of silio standa	con: rd recov	ery rect	ifier					
	6 -	Vol	tage rati	ng: volta	age cod	e x 100	= V <sub>RRM</sub>	1	12 = 1	1200 V	
	7 -	S =	surface	mounta	able						
	8 -	L =	L = tape and reel (left oriented), for different orientation contact factor								
	9 -	H =	AEC-Q	101 qua	alified						
	10 -	M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lea	ad (Pb)-fi	

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS12SLHM3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96317					

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# **Outline Dimensions**

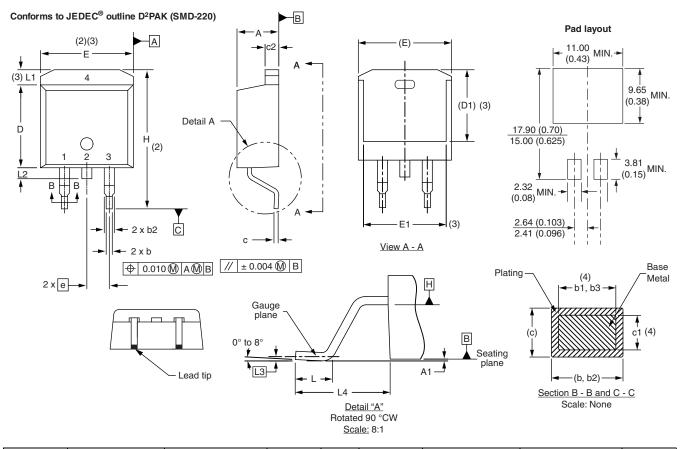


D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches

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SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		NOTES		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070			
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC		0.25 BSC 0.010 BSC				
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208			

### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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